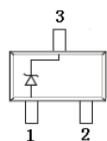


ZENER DIODES

FEATURES

- Planar Die construction
- 500mW Power Dissipation
- Zener Voltages from 2.4V - 39V
- Ideally Suited for Automated Assembly Processes



MMBZ52XXB series



Parameter	Symbol	Value	Units
Power Dissipation (Notes A) at 75°C	P _D	500	mW
Peak Forward Surge Current, 8.3ms single half sine-wave superimposed on rated load (JEDEC method) (Notes B)	I _{FSM}	4.0	Amps
Operating Junction and Storage Temperature Range	T _J	-55 to +150	°C

NOTES:

A. Mounted on 5.0mm²(.013mm thick) land areas.

B. Measured on 8.3ms, single half sine-wave or equivalent square wave, duty cycle = 4 pulses per minute maximum.

MMBZ52XXB series

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Part Number	Nominal Zener Voltage			Max. Zener Impedance			Max Reverse Leakage Current		Typical Temp. Coefficient	Max. Zener Current	
	Vz @ IzT			ZzT @ IzT		Zzk @ Izk		Ir @ VR			
	Nom. V	Min. V	Max. V	Ω	mA	Ω	mA	nA	V		
500 mWatts Zener Diodes											
MMBZ5221B	2.4	2.28	2.52	30	20	1200	0.25	100	1	-0.070	
MMBZ5222B	2.5	2.38	2.63	30	20	1250	0.25	100	1	-0.065	
MMBZ5223B	2.7	2.57	2.84	30	20	1300	0.25	75	1	-0.060	
MMBZ5225B	3	2.85	3.15	30	20	1600	0.25	50	1	-0.055	
MMBZ5226B	3.3	3.14	3.47	28	20	1600	0.25	25	1	0.030	
MMBZ5227B	3.6	3.42	3.78	24	20	1700	0.25	15	1	0.030	
MMBZ5228B	3.9	3.71	4.1	23	20	1900	0.25	10	1	+0.038	
MMBZ5229B	4.3	4.09	4.52	22	20	2000	0.25	5	1	+0.038	
MMBZ5230B	4.7	4.47	4.94	19	20	1900	0.25	5	2	+0.045	
MMBZ5231B	5.1	4.85	5.36	17	20	1600	0.25	5	2	+0.050	
MMBZ5232B	5.6	5.32	5.88	11	20	1600	0.25	5	3	+0.058	
MMBZ5234B	6.2	5.89	6.51	7	20	1000	0.25	5	4	+0.062	
MMBZ5235B	6.8	6.46	7.14	5	20	750	0.25	3	5	+0.065	
MMBZ5236B	7.5	7.13	7.88	6	20	500	0.25	3	6	+0.068	
MMBZ5237B	8.2	7.79	8.61	8	20	500	0.25	3	6	+0.075	
MMBZ5239B	9.1	8.65	9.56	10	20	600	0.25	3	6.5	+0.076	
MMBZ5240B	10	9.5	10.5	17	20	600	0.25	3	8	+0.077	
MMBZ5241B	11	10.45	11.55	22	20	600	0.25	3	8.4	+0.079	
MMBZ5242B	12	11.4	12.6	30	20	600	0.25	2	9.1	+0.082	
MMBZ5243B	13	12.35	13.65	13	9.5	600	0.25	1	9.9	+0.082	
MMBZ5245B	15	14.25	15.75	16	8.5	600	0.25	0.5	11	+0.083	
MMBZ5246B	16	15.2	16.8	17	7.8	600	0.25	0.1	12	+0.084	
MMBZ5248B	18	17.1	18.9	21	7	600	0.25	0.1	14	+0.085	
MMBZ5250B	20	19	21	25	6.2	600	0.25	0.1	15	+0.086	
MMBZ5251B	22	20.9	23.1	29	5.6	600	0.25	0.1	17	+0.086	
MMBZ5252B	24	22.8	25.2	33	5.2	600	0.25	0.1	18	+0.087	
MMBZ5254B	27	25.65	28.35	41	5	600	0.25	0.1	21	+0.087	
MMBZ5255B	28	26.6	29.4	44	4.5	600	0.25	0.1	21	+0.089	
MMBZ5256B	30	28.5	31.5	49	4.2	600	0.25	0.1	23	+0.090	
MMBZ5257B	33	31.35	34.65	58	3.8	700	0.25	0.1	25	+0.091	
MMBZ5258B	36	34.2	37.8	70	3.4	700	0.25	0.1	27	+0.091	
MMBZ5259B	39	37.05	40.95	80	3.2	800	0.25	0.1	30	+0.092	
										11.6	

NOTE:

1. Tolerance and Type Number Designation. The type numbers listed have a standard tolerance on the nominal zener voltage of ±5%.

2. Specials Available Include:

A. Nominal zener voltages between the voltages shown and tighter voltage tolerances.

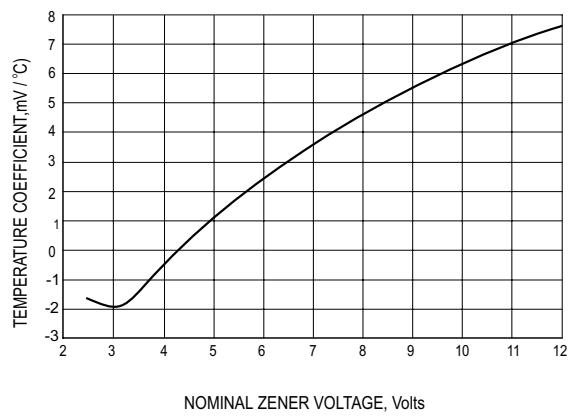
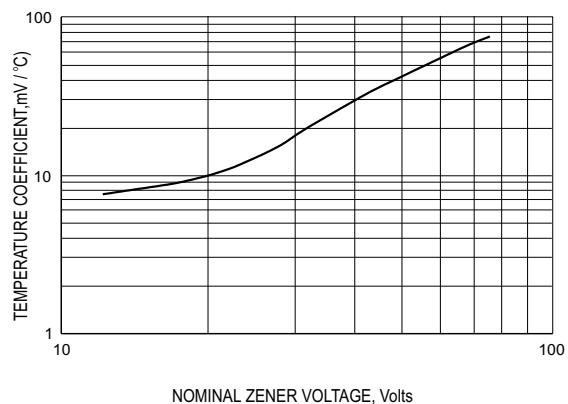
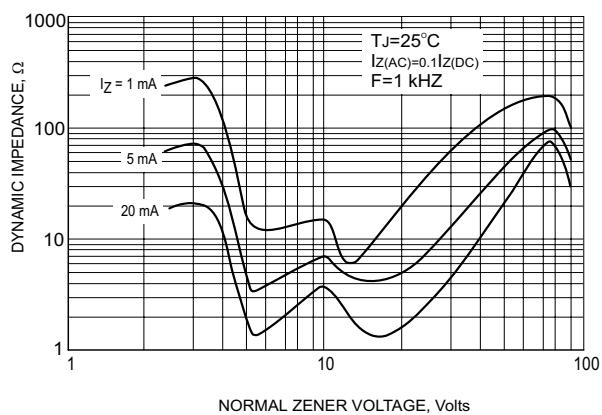
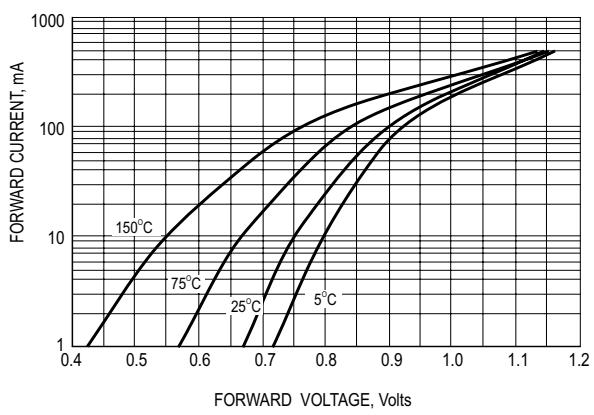
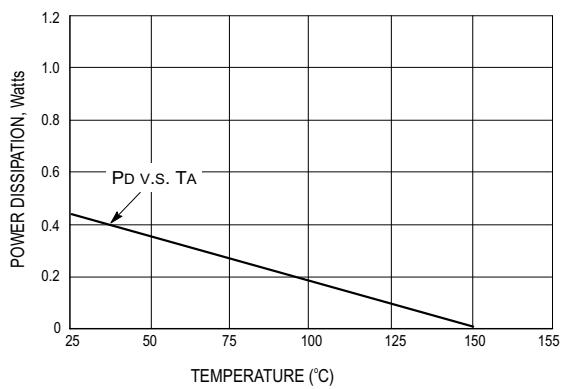
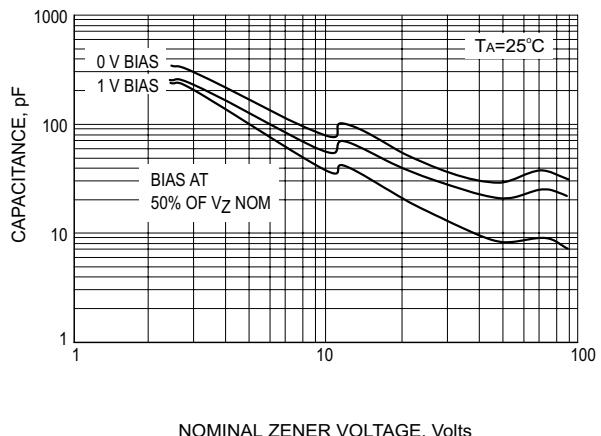
B. Matched sets.

3. Zener Voltage (Vz) Measurement. Guarantees the zener voltage when measured at 90 seconds while maintaining the lead temperature (T_L) at 30°C, from the diode body.

4. Zener Impedance (Zz) Derivation. The zener impedance is derived from the 60 cycle ac voltage, which results when an AC current having an rms value equal to 10% of the dc zener current (I_{zT} or I_{zk}) is superimposed on I_{zT} or I_{zk}.

5. Surge Current (Ir) Non-Repetitive. The rating listed in the electrical characteristics table is maximum peak, non-repetitive, reverse surge current of 1/2 square wave or equivalent sine wave pulse of 1/120 second duration superimposed on the test current, I_{zT}, per JEDEC registration; however, actual device capability is as described in Figure 5.

MMBZ52XXB series


TYPICAL REVERSE CURRENT

STEADY STATE POWER DERATING

EFFECT OF ZENER VOLTAGE ON ZENER IMPEDANCE

TYPICAL FORWARD VOLTAGE

STEADY STATE POWER DERATING

TYPICAL CAPACITANCE